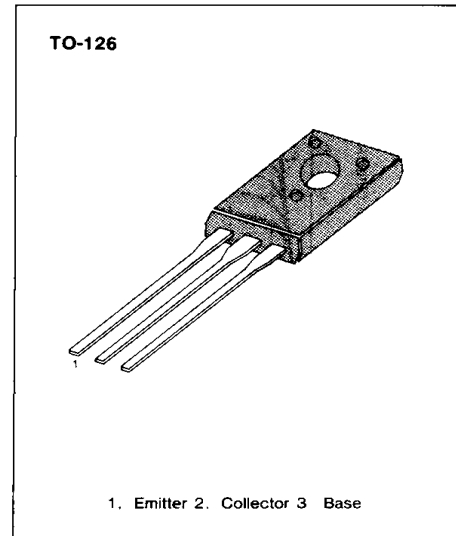


COLLECTOR-EMITTER SUSTAINING VOLTAGE
LOW COLLECTOR-EMITTER SATURATION
VOLTAGE
HIGH CURRENT GAIN-BANDWIDTH
PRODUCT-MIN $f_T=65\text{MHz}$ @ $I_C=100\text{mA}$

Complementary to MJE210

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

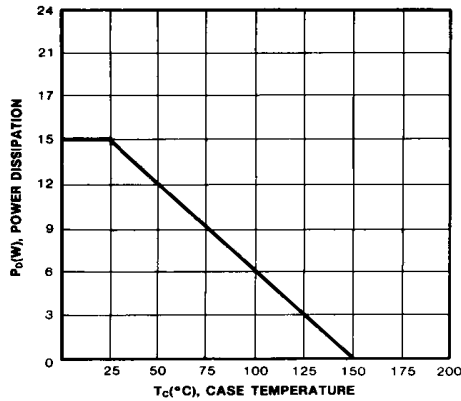
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	8	V
Collector Current	I_C	5	A
Collector Dissipation	P_C	15	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-65\sim 150$	$^\circ\text{C}$



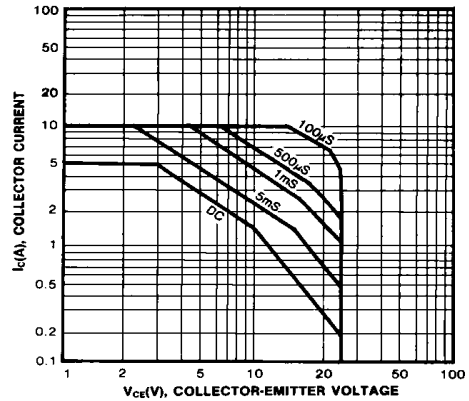
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C=10\text{mA}, I_B=0$	25		V
Collector Cutoff Current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$		100	nA
		$V_{CB}=40\text{V}, I_E=0, T_j=125^\circ\text{C}$		100	μA
Emitter Cutoff Current	I_{EBO}	$V_{BE}=8\text{V}, I_C=0$		100	nA
DC Current Gain	h_{FE}	$V_{CE}=1\text{V}, I_C=500\text{mA}$	70		
		$V_{CE}=1\text{V}, I_C=2\text{A}$	45	180	
		$V_{CE}=2\text{V}, I_C=5\text{A}$	10		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.3	V
		$I_C=2\text{A}, I_B=200\text{mA}$		0.75	V
		$I_C=5\text{A}, I_B=1\text{A}$		1.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5\text{A}, I_B=1\text{A}$		2.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=1\text{V}, I_C=2\text{A}$		1.6	V
Current Gain-Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=10\text{MHz}$	65		MHz
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$		80	pF

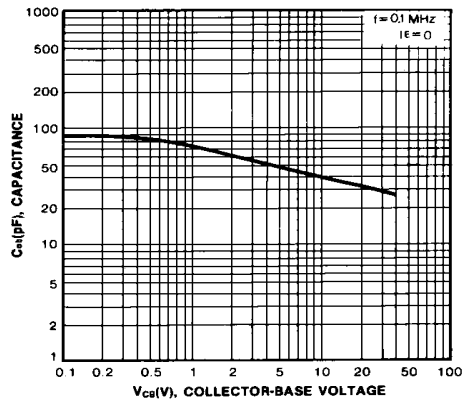
POWER DERATING



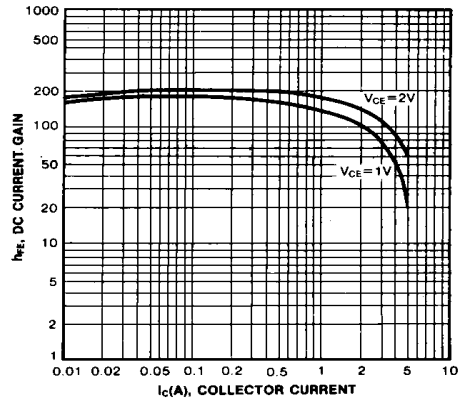
FORWARD BIAS SAFE OPERATING AREA



COLLECTOR OUTPUT CAPACITANCE



DC CURRENT GAIN



COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE

